Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = −10V	Steady State	T_A = +25°C	I_D	-4.3	A
	t < 10s	T_A = +25°C	I_D	-5.8	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	-2.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-13	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.25	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	100	°C/W
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	86	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	15.6	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	µA	V_{GS} = 0V, V_{DS} = -30V
Gate-Body Leakage Current	I_{GSS}	—	—	±100 ±800	nA	V_{GS} = ±20V, V_{DS} = 0V V_{GS} = ±25V, V_{DS} = 0V
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	—	-2.1	V	V_{GS} = V_{DS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— —	— —	45 65	mΩ	V_{GS} = -10V, I_D = -5A V_{GS} = -4.5V, I_D = -4.2A
Forward Transconductance	g_{FS}	—	8	—	s	V_{DS} = -10V, I_D = -4.3A
Diode Forward Voltage	V_{SD}	—	—	-1.2	V	V_{GS} = 0V, I_S = -1.7A
DYNAMIC PARAMETERS (Note 9)						
Input Capacitance	C_{iss}	—	948	—	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz
Output Capacitance	C_{oss}	—	105	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	100	—	pF	
SWITCHING CHARACTERISTICS (Note 9)						
Total Gate Charge	Q_g	—	10.1	—	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -6A
	Q_g	—	21.1	—	nC	V_{DS} = -15V, V_{GS} = -10V, I_D = -6A
Gate-Source Charge	Q_{gs}	—	2.8	—		
Gate-Drain Charge	Q_{gd}	—	3.2	—		
Gate Resistance	R_g	—	13.15	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Turn-On Delay Time	$t_{D(ON)}$	—	10.2	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_g = 6.0Ω
Rise Time	t_R	—	6.6	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	50.1	—		
Fall Time	t_F	—	22.3	—		

Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

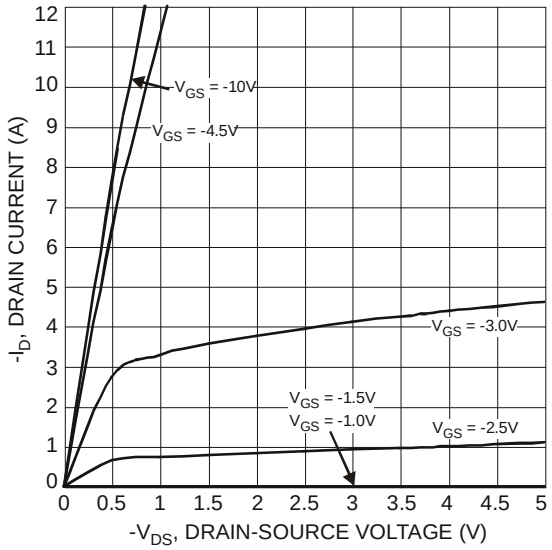


Fig. 1 Typical Output Characteristics

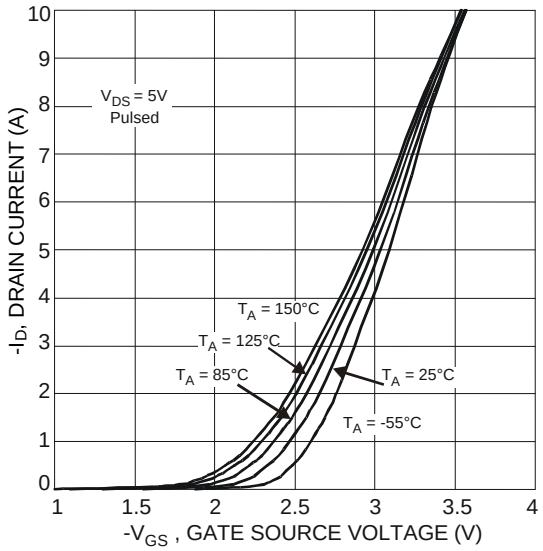


Fig. 2 Typical Transfer Characteristics

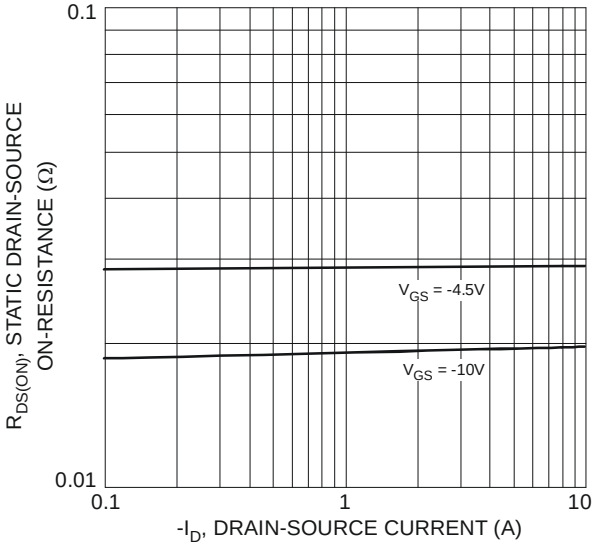


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

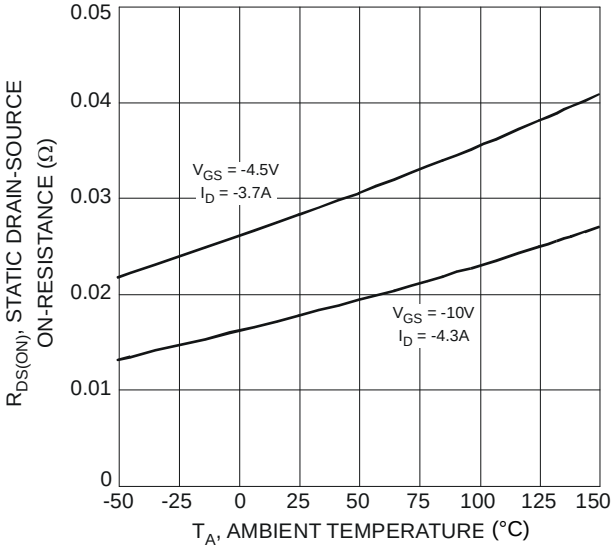


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

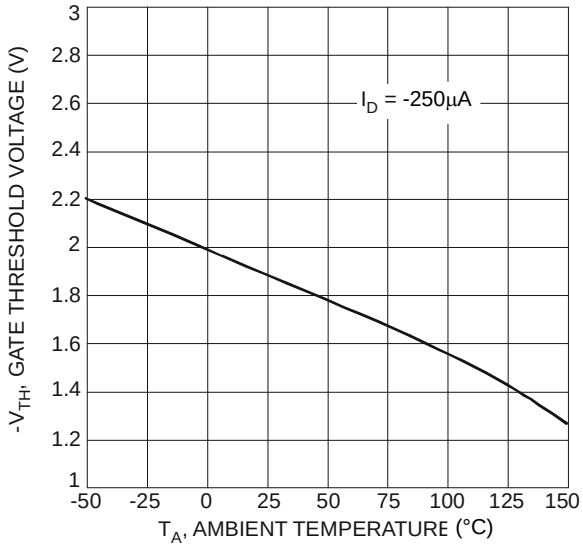


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

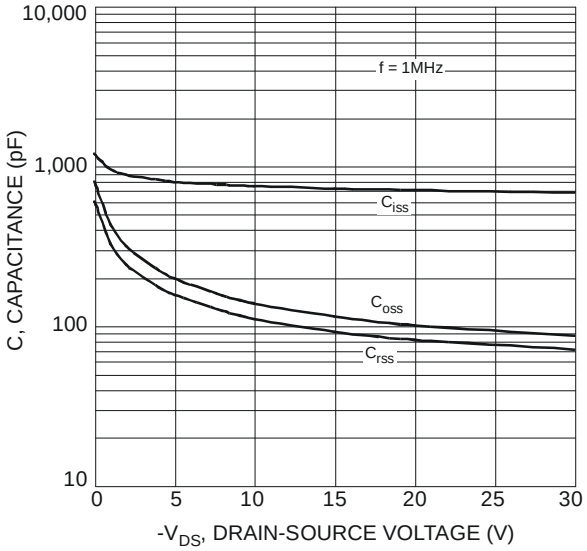


Fig. 6 Typical Total Capacitance

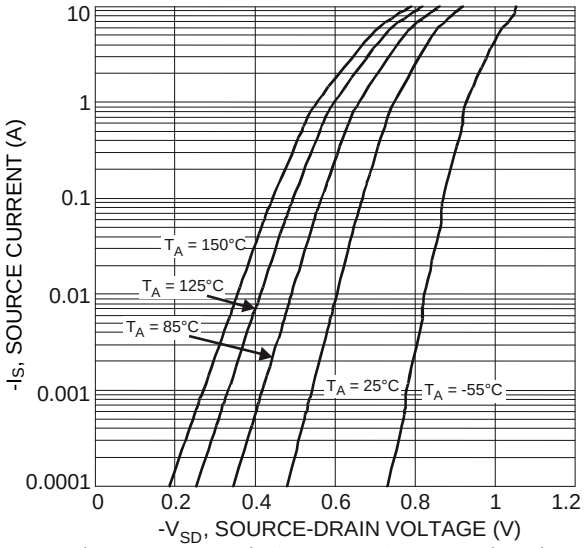


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

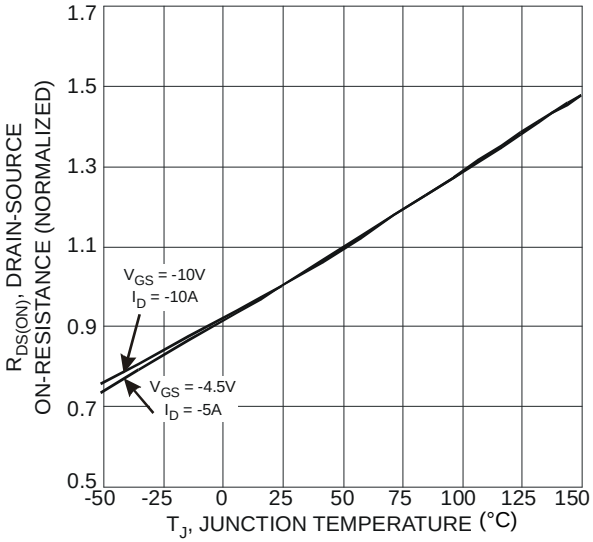


Fig. 8 On-Resistance Variation with Temperature

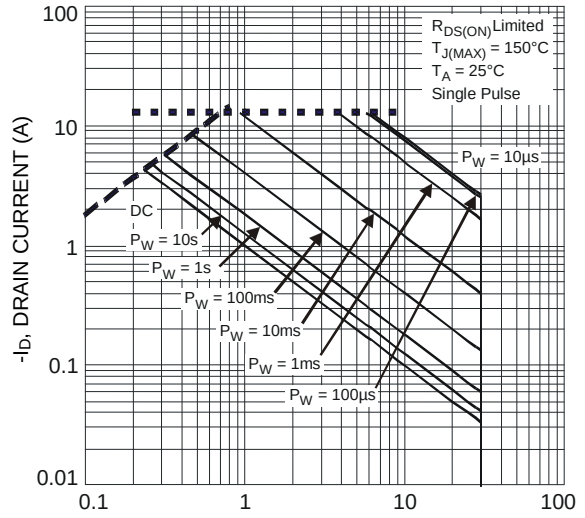


Fig. 9 Safe Operation Area

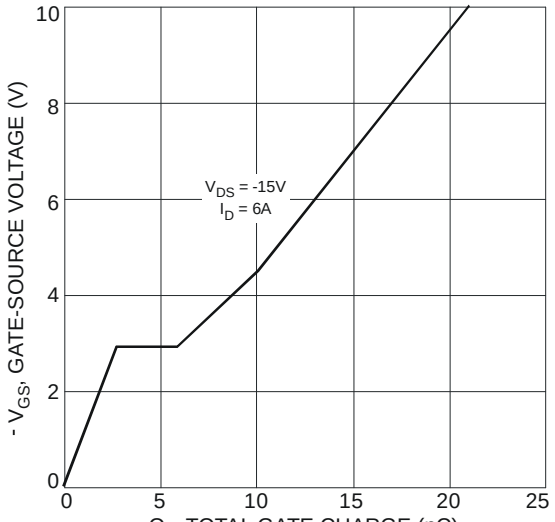


Fig. 10 Gate-Charge Characteristics

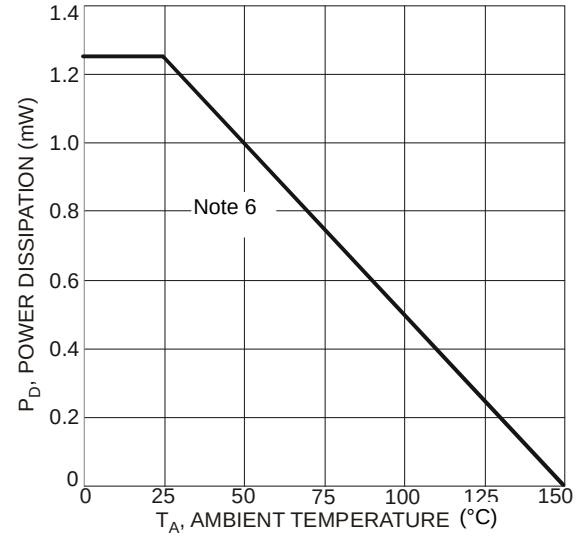


Fig. 11 Power Dissipation vs. Ambient Temperature

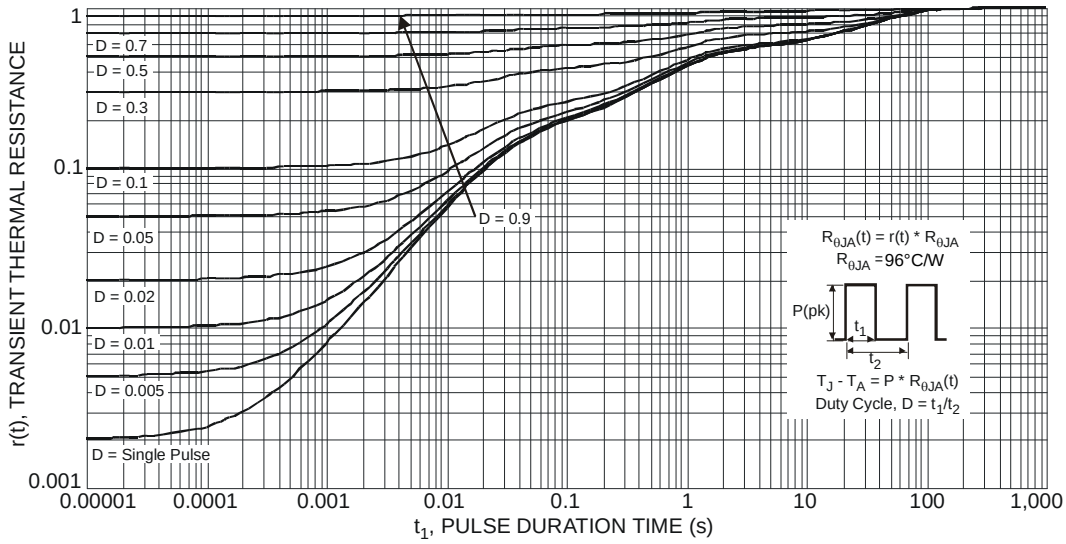
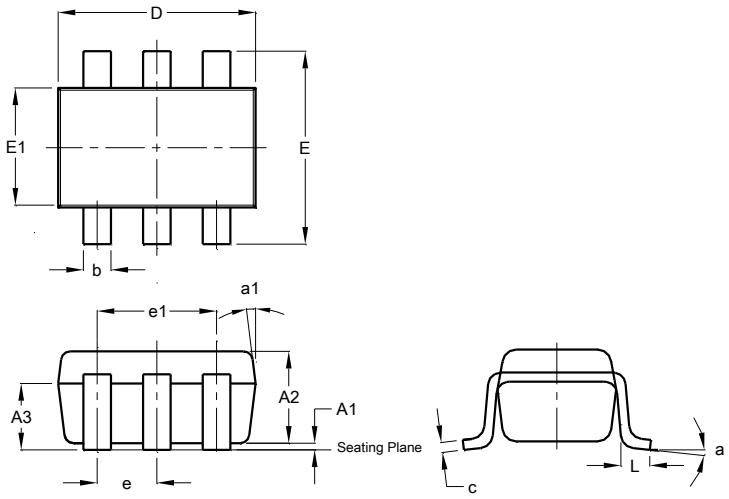


Fig. 12 Transient Thermal Response

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

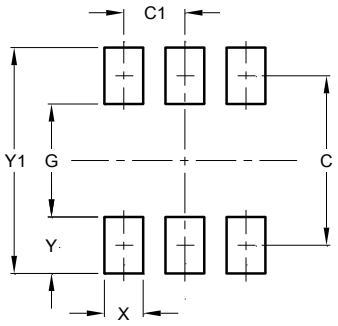


SOT26			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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